

# H5N5001FM

Silicon N Channel MOS FET  
High Speed Power Switching

# HITACHI

ADE-208-1380 (Z)

1st. Edition

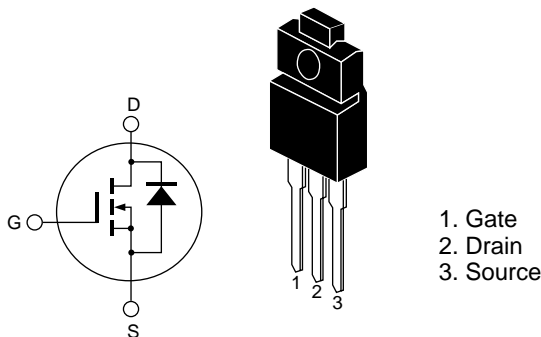
Mar. 2001

## Features

- Low on-resistance :  $R_{DS(on)} = 1.1\Omega$  typ.
- Low leakage current :  $I_{DSS} = 1\mu A$  max (at  $V_{DS} = 500$  V)
- High speed switching :  $t_f = 15$  ns typ (at  $V_{GS} = 10$  V,  $V_{DD} = 250$  V,  $I_D = 2.5$  A)
- Low gate charge :  $Q_g = 15$  nC typ (at  $V_{DD} = 400$  V,  $V_{GS} = 10$  V,  $I_D = 5$  A)
- Avalanche ratings

## Outline

TO-220FM



## Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	500	V
Gate to source voltage	$V_{GSS}$	±30	V
Drain current	$I_D$	5	A
Drain peak current	$I_{D(pulse)}^{Note1}$	20	A
Body-drain diode reverse drain current	$I_{DR}$	5	A
Body-drain diode reverse drain peak current	$I_{DR(pulse)}^{Note1}$	20	A
Avalanche current	$I_{AP}^{Note3}$	5	A
Channel dissipation	$Pch^{Note2}$	30	W
Channel to case Thermal Impedance	$\theta_{ch-c}$	4.17	°C/W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

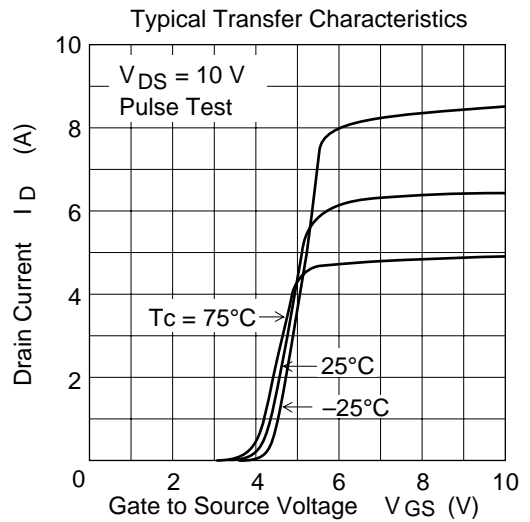
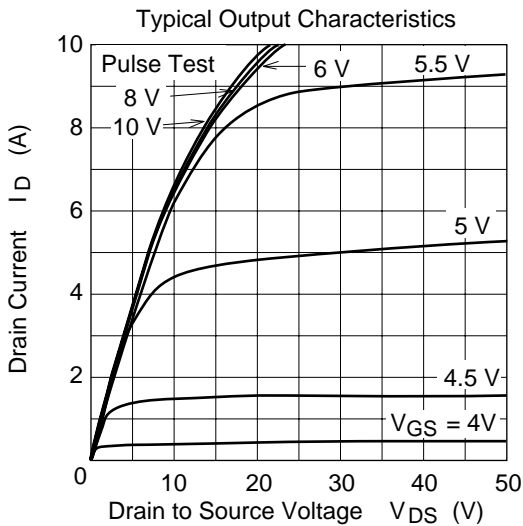
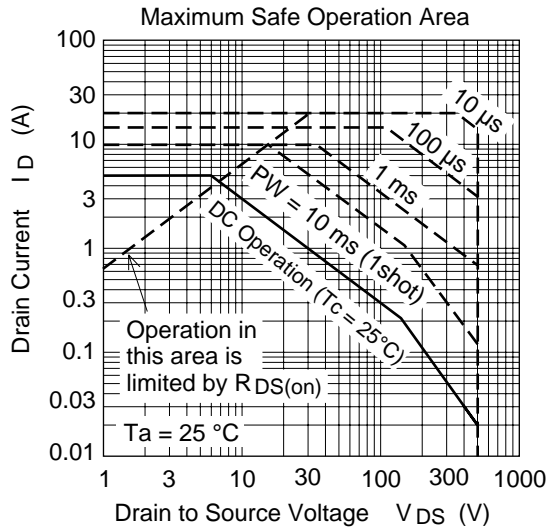
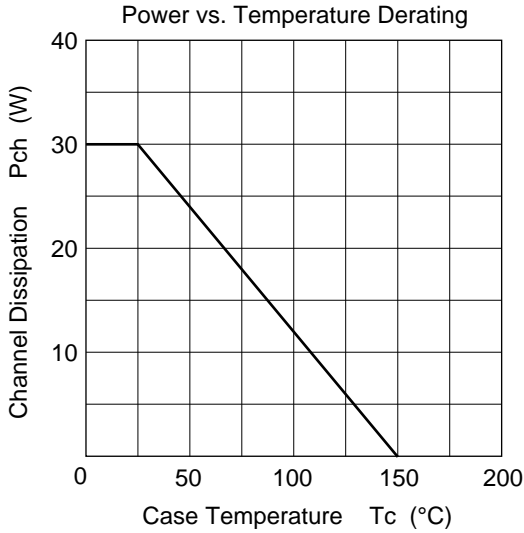
Note: 1.  $PW \leq 10\mu s$ , duty cycle  $\leq 1\%$   
2. Value at  $T_c = 25^\circ C$   
3.  $T_{ch} \leq 150^\circ C$

**Electrical Characteristics** (Ta = 25°C)

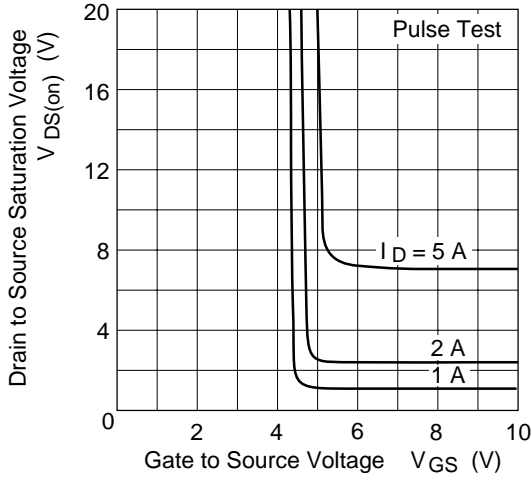
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	500	—	—	V	$I_D = 10\text{mA}$ , $V_{GS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 0.1$	$\mu\text{A}$	$V_{GS} = \pm 30\text{V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 500\text{V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	—	4.0	V	$I_D = 1\text{mA}$ , $V_{DS} = 10\text{V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	1.1	1.5	$\Omega$	$I_D = 2.5\text{A}$ , $V_{GS} = 10\text{V}$ <sup>Note4</sup>
Forward transfer admittance	$ y_{fs} $	3.0	4.5	—	S	$I_D = 2.5\text{A}$ , $V_{DS} = 10\text{V}$ <sup>Note4</sup>
Input capacitance	Ciss	—	580	—	pF	$V_{DS} = 25\text{V}$
Output capacitance	Coss	—	70	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	13	—	pF	$f = 1\text{MHz}$
Turn-on delay time	$t_{d(on)}$	—	20	—	ns	$I_D = 2.5\text{A}$
Rise time	$t_r$	—	15	—	ns	$V_{GS} = 10\text{V}$
Turn-off delay time	$t_{d(off)}$	—	65	—	ns	$R_L = 100\Omega$
Fall time	$t_f$	—	15	—	ns	$R_g = 10\Omega$
Total gate charge	Qg	—	15	—	nC	$V_{DD} = 400\text{V}$
Gate to source charge	Qgs	—	3	—	nC	$V_{GS} = 10\text{V}$
Gate to drain charge	Qgd	—	8	—	nC	$I_D = 5\text{A}$
Body–drain diode forward voltage	$V_{DF}$	—	0.85	1.3	V	$I_F = 5\text{A}$ , $V_{GS} = 0$
Body–drain diode reverse recovery time	$t_{rr}$	—	400	—	ns	$I_F = 5\text{A}$ , $V_{GS} = 0$ $diF/dt = 100\text{A}/\mu\text{s}$
Body–drain diode reverse recovery charge	$Q_{rr}$	—	1.5	—	$\mu\text{C}$	

Note: 4. Pulse test

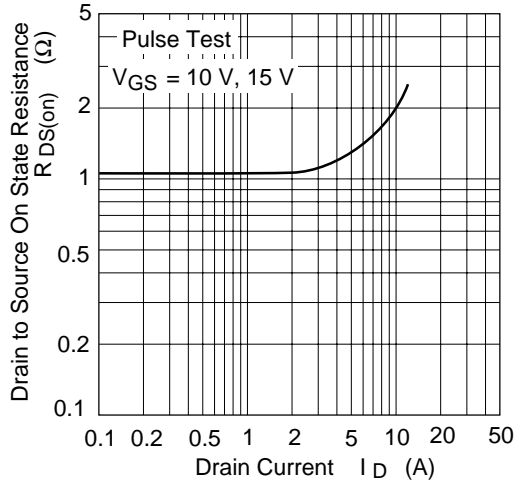
## Main Characteristics



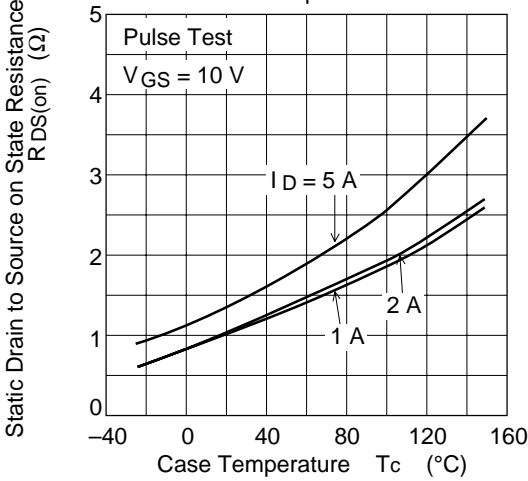
Drain to Source Saturation Voltage vs. Gate to Source Voltage



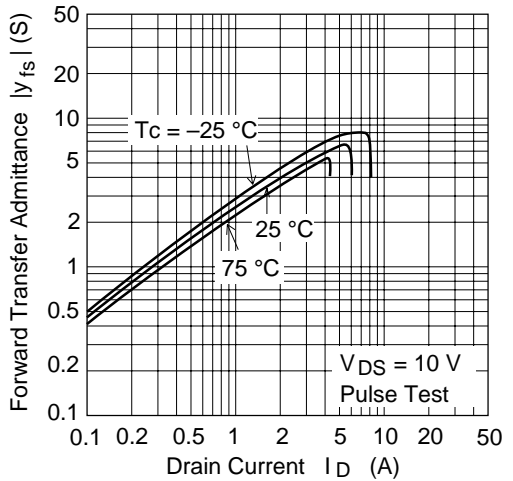
Static Drain to Source on State Resistance vs. Drain Current



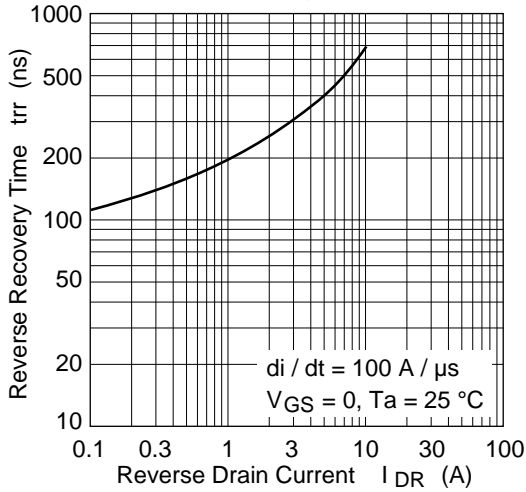
Static Drain to Source on State Resistance vs. Temperature



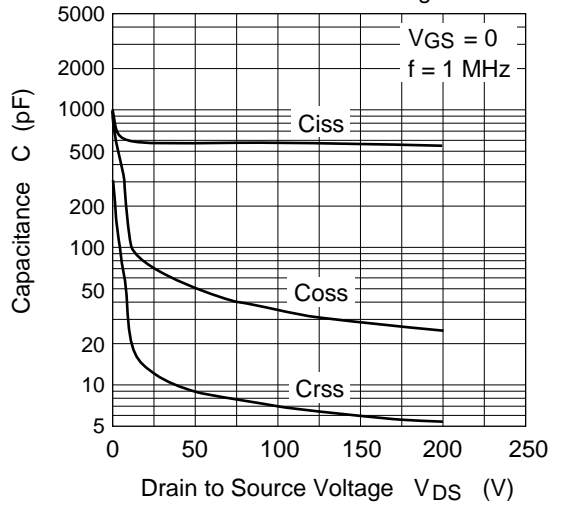
Forward Transfer Admittance vs. Drain Current



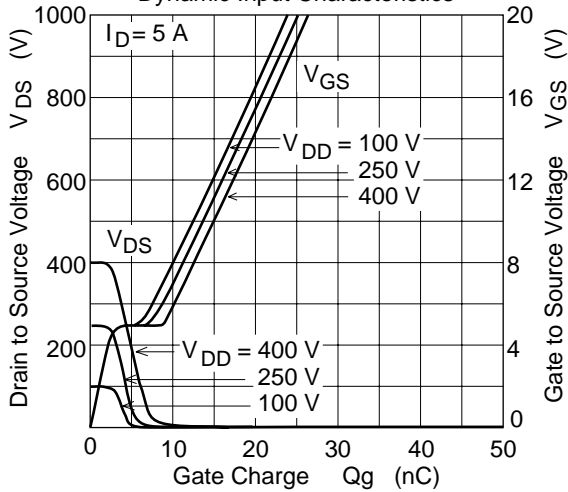
Body-Drain Diode Reverse Recovery Time



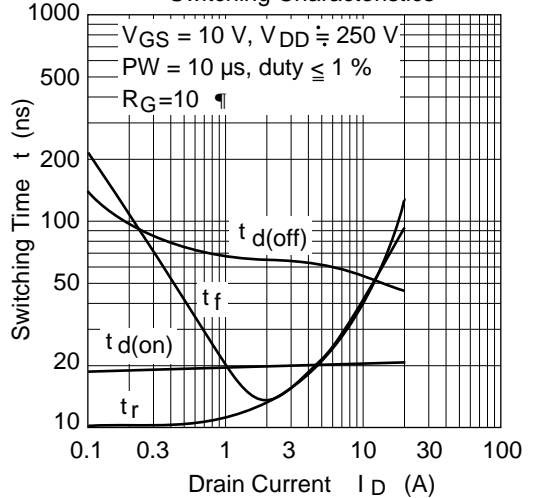
Typical Capacitance vs. Drain to Source Voltage



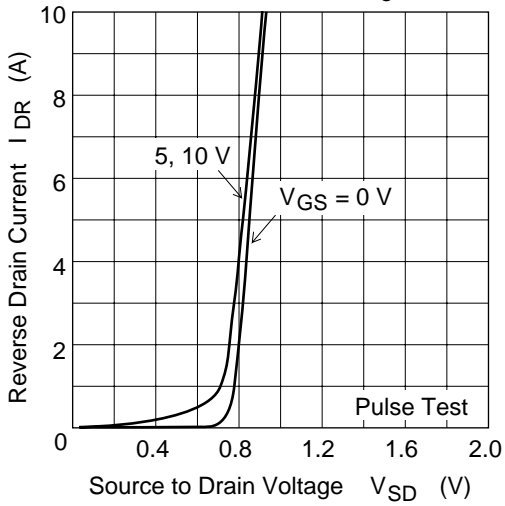
Dynamic Input Characteristics



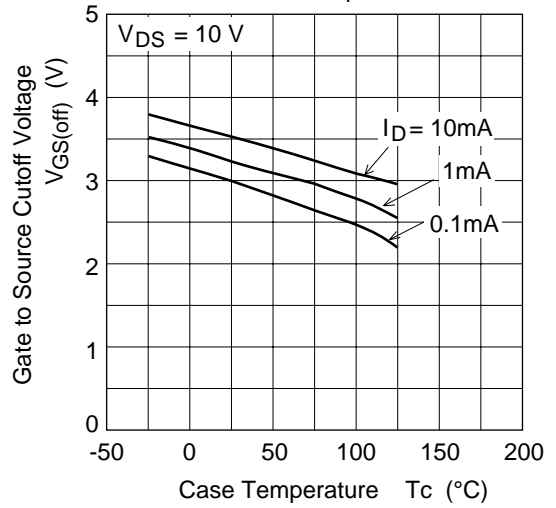
Switching Characteristics



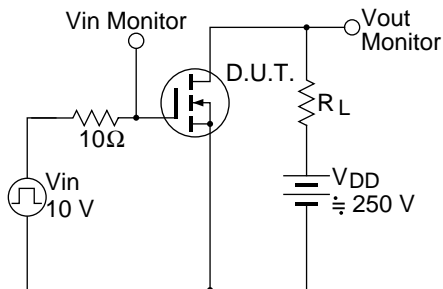
Reverse Drain Current vs. Source to Drain Voltage



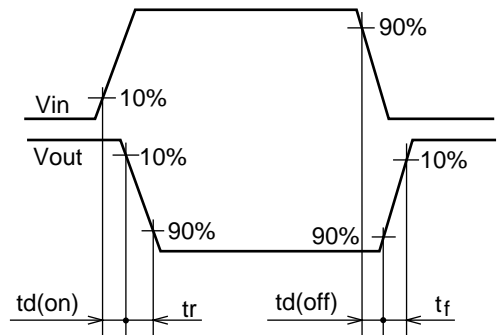
Gate to Source Cutoff Voltage vs. Case Temperature

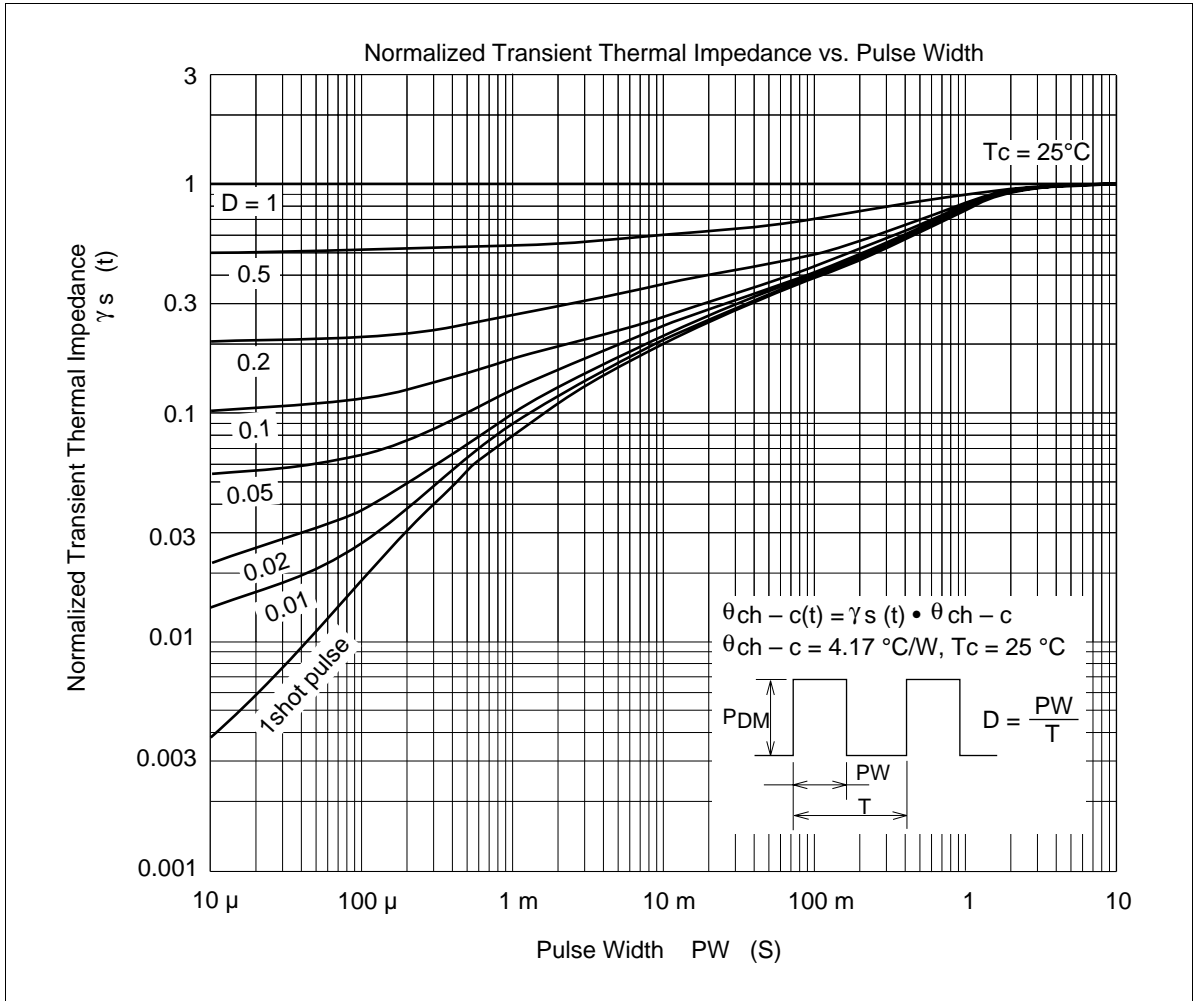


Switching Time Test Circuit



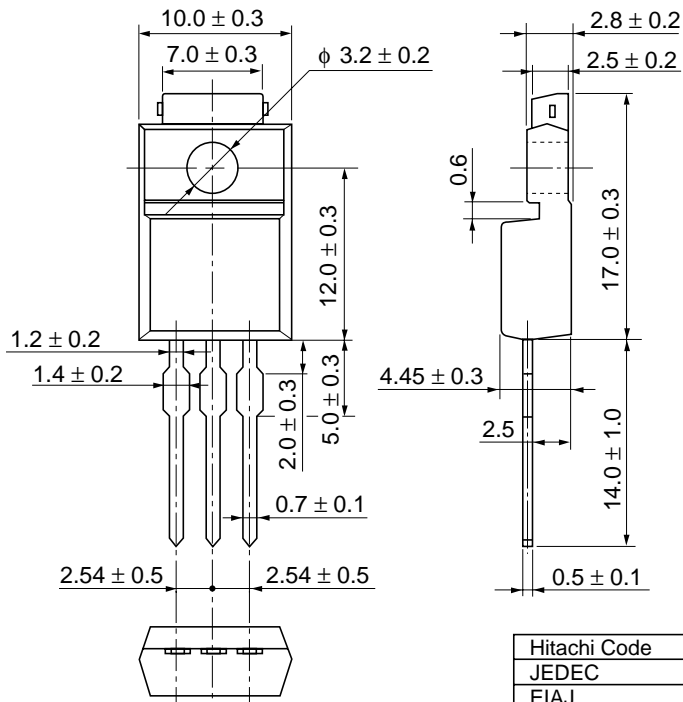
Waveform



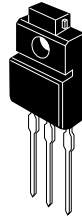




Package Dimensions



As of January, 2001  
Unit: mm



Hitachi Code	TO-220FM
JEDEC	—
EIAJ	Conforms
Mass (reference value)	1.8 g

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